



#### 1.8/3.3V High-Bandwidth 6-Channel, 2:1 Mux/DeMux

#### Features

- CMOS Technology for Bus and Analog Applications
- Low Propagation Delay
- Low Typical On-Resistance: 5Ω
- Signal Passing Bandwidth, 380 MHz
- Wide V<sub>DD</sub> Range: 1.65V to 3.6V
- Rail-to-Rail Signal Range
- High Off Isolation: -66dB @ 10MHz
- Crosstalk Rejection Reduces Signal Distortion: -60dB @ 10MHz
- Break-Before-Make Switching
- Supports AEC-Q100 Grade 2: -40°C to 105°C
- ESD Protection : 2.5kV(HBM)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES<sup>™</sup> PI3A27518Q is suitable for automotive applications requiring specific change control; this part is AEC-Q100 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities. https://www.diodes.com/quality/product-definitions/
- Packaging (Pb-free & Green):
  24-pin, Wettable VQFN (ZDW), 4mm x 4mm

## Applications

- SD-SDIO and MMC Two-Port MUX
- qSPI Two-Port MUX
- ADAS

# Description

The PI3A27518Q is a 6-channel, 1:2 multiplexer / demultiplexer. The COMx port can be configured to connect with NOx or NCx ports in 4 different modes (refer to Truth Table for details)

The PI3A27518Q has a wide operating voltage range, very low power consumption and small packaging.

It can be used as an analog switch or as a low-delay bus switch. Specified over a wide operating power supply voltage, 1.65V to 3.6V, the PI3A27518Q has an On-Resistance of  $5\Omega$  at +3.3V.

Break-before-make switching prevents both switches being enabled simultaneously. This eliminates signal disruption during switching.

Notes:

<sup>1.</sup> No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

<sup>2.</sup> See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

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# **Block Diagram**



# **Function Table**

	Select Input		Function	
ĒN	IN1	IN2	Function	
1	Х	Х	All Channels are OFF	
0	0	0	NC <sub>1,2,3</sub> Connected to COM <sub>1,2,3</sub> NC <sub>4,5,6</sub> Connected to COM <sub>4,5,6</sub>	
0	1	0	NO <sub>1,2,3</sub> Connected to COM <sub>1,2,3</sub> NC <sub>4,5,6</sub> Connected to COM <sub>4,5,6</sub>	
0	0	1	NC <sub>1,2,3</sub> Connected to COM <sub>1,2,3</sub> NO <sub>4,5,6</sub> Connected to COM <sub>4,5,6</sub>	
0	1	1	NO <sub>1,2,3</sub> Connected to COM <sub>1,2,3</sub> NO <sub>4,5,6</sub> Connected to COM <sub>4,5,6</sub>	





# **Pin Configuration**



## **Pin Description**

Pin#	Name	Description
1	COM1	Common Signal Path
2	GND	Ground
3	COM2	Common Signal Path
4	COM3	Common Signal Path
5	VDD	Positive Power Supply
6	COM4	Common Signal Path
7	COM5	Common Signal Path
8	NO1	Signal Path – Normal Open
9	COM6	Common Signal Path
10	NO2	Data Port (Normally open)
11	IN2	Select Input 2
12	NO3	Signal Path – Normal Open
13	NO6	Signal Path – Normal Open
14	NO4	Signal Path – Normal Open
15	NO5	Signal Path – Normal Open
16	NC5	Signal Path – Normal Closed
17	ĒN	Enable Input, Low Active
18	NC4	Signal Path – Normal Closed
19	NC6	Signal Path – Normal Closed
20	NC3	Signal Path – Normal Closed
21	IN1	Select Input 1
22	NC2	Signal Path – Normal Closed
23	NC1	Signal Path – Normal Closed
24	N.C	No connect





#### **Maximum Ratings**

Storage Temperature	-65°C to +150°C
Ambient Temperature with Power Applied	-40°C to +105°C
Supply Voltage V <sub>DD</sub>	0.5Vto +4.6V
Control Input Voltage V <sub>INx</sub>	0Vto +4.6V
DC Input Voltage V <sub>INPUT</sub>	0.5Vto +4.6V
Continuous Current NO_NC_COM	±50mA
ESD(HBM)	2.5kV
ESD(CDM)	1.5kV

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

The input and output negative voltage ratings may be exceeded if the input and output diode current ratings are observed. Control input must be held HIGH or LOW; it must not float.

# **Recommended Operating Conditions**

Symbol	Parameter	Min.	Тур.	Max.	Unit
V <sub>DD</sub>	Operating Voltage	1.65	-	3.6	V
V <sub>IN</sub>	Control Input Voltage	0	-	V <sub>DD</sub>	V
VINPUT	Switch Input Voltage	-0.3	-	V <sub>DD</sub>	V
T <sub>A</sub>	Operating Temperature	-40	25	105	°C

## **DC Electrical Characteristics**

Symbol	Parameter	Test Conditions	TEMP	Min.	Тур.	Max.	Units
ANALOG	<b>SWITCH</b>						
V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>	Analog Signal Range		-40°C to 105°C	0	-	$V_{\text{DD}}$	V
		$V_{DD} = 3V, I_{COM} = -32mA,$	+25°C	-	4.4	5.2	
R <sub>ON</sub>	On-Resistance	$0 \le V_{NO} \text{ or } V_{NC} \le V_{DD},$ <i>Test Circuit 1</i>	-40°C to 105°C	-	-	7.6	Ω
	On-Resistance	$V_{DD} = 3V, I_{COM} = -32mA,$	+25°C	-	0.3	0.7	
$\Delta R_{ON}$	Match Between Channels	$V_{NO}$ or $V_{NC} = 2.1V$ , Test Circuit 1	-40°C to 105°C	-	-	0.8	Ω
		$V_{DD} = 3.3V,$	+25°C	-	0.95	2.1	
R <sub>ONF</sub>	On-Resistance Flatness	$I_{COM} = -32 \text{mA}, V_{NO} =$ 0.15V or $V_{NC} = 3.15V$ , Test Circuit 1	-40°C to 105°C	-	-	2.3	Ω
I <sub>OFF (NO)</sub> or I <sub>OFF (NC)</sub>	NC/NO Channel- Off Leakage Current	$V_{DD} = 3.6V, V_{NO} \text{ or } V_{NC} = 3V \& V_{COM} = 1V \text{ or } V_{NO} \text{ or } V_{NC} = 1V \& V_{COM} = 3V$	-40°C to 105°C	-2	-	2	μΑ
I <sub>OFF (COM)</sub>	COM Channel-Off Leakage Current	$V_{DD} = 3.6V, V_{NO} \text{ or } V_{NC} = 3V \& V_{COM} = 1V \text{ or } V_{NO} \text{ or } V_{NC} = 1V \& V_{COM} = 3V$	-40°C to 105°C	-2	-	2	μΑ
I <sub>OFF (NO)</sub> or I <sub>OFF (NC)</sub>	NC/NO POWER- Off Leakage Current		-40°C to 105°C	-12	-	12	μΑ
I <sub>OFF (COM)</sub>	COM POWER-Off Leakage Current	$V_{DD} = 0V, V_{NO} \text{ or } V_{NC} = 3.6V \& V_{COM} = 0V \text{ or } V_{NO} \text{ or } V_{NC} = 0V \& V_{COM} = 3.6V$	-40°C to 105°C	-12	-	12	μΑ
I <sub>ON</sub> (NO)	Channel-On Leak-	$V_{DD} = 3.6 V_{,}$	-40°C to 105°C	-7	-	7	μA



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Symbol	Parameter	Test Conditions	ТЕМР	Min.	Тур.	Max.	Units
or	age Current	$V_{\rm NO} \text{ or } V_{\rm NC} = 3V \& V_{\rm COM}$					
$I_{ON}$ (NC)	(NO/NC)	= open or $V_{NO}$ or $V_{NC}$ =					
		$1V \& V_{COM} = open$					
		$V_{DD} = 3.6 V,$					
Ion	Channel-On Leak-	$V_{NO}$ or $V_{NC}$ = open &	-40°C to 105°C	-7	-	7	μA
(COM)	age Current (COM)	$V_{COM} = 3V$ or $V_{NO}$ or $V_{NC}$	10 0 10 105 0	/		,	μι
		= open & $V_{COM} = 1V$					
DIGITAL				1	1		1
V <sub>IH</sub>	Input Logic High	-	-40°C to 105°C	0.8	-	3.6	V
V <sub>IL</sub>	Input Logic Low	-	-40°C to 105°C	0	-	0.2	•
I <sub>IN</sub>	IN Input Leakage	$V_{DD} = 3.6V, V_{IN} = 0$ or	-40°C to 105°C	-2.5	_	2.5	μA
	Current	3.6V	10 0 10 105 0	2.5		2.0	μ
DYNAMI	C CHARACTERIST						
		$V_{DD} = 3.3 V, V_{COM} = V_{DD},$					
		$R_L = 50\Omega, C_L = 35pF$	+25°C	-	11.5	30.0	ns
ton	Turn-On Time	See Test Circuit Figure 2.					
UN		$V_{DD} = 3V$ to 3.6V, $V_{COM} =$					
		$V_{DD}$ , $R_L = 50\Omega$ , $C_L = 35pF$	-40°C to 105°C	-	-	30.0	ns
		See Test Circuit Figure 2.					
		$V_{DD} = 3.3 V, V_{COM} = V_{DD},$					
		$R_L = 50\Omega, C_L = 35pF$	+25°C	-	7.6	30.0	ns
toff	Turn-Off Time	See Test Circuit Figure 2.					
		$V_{DD} = 3V$ to 3.6V, $V_{COM} =$	4000 10500			20.0	
		$V_{DD}$ , $R_L = 50\Omega$ , $C_L = 35pF$	-40°C to 105°C	-	-	30.0	ns
		See Test Circuit Figure 2.					
		$V_{DD} = 3.3V, V_{NC} = V_{NO} =$	10500	4.0	6.5	20.0	
		$V_{DD}, R_L = 50\Omega, C_L = 35pF$	+25°C	4.0	6.5	20.0	ns
	Break-Before-Make	See Test Circuit Figure 3.					
t <sub>D</sub>	Delay	$V_{DD} = 3V$ to 3.6V, $V_{NC} =$					
		$V_{NO} = V_{DD}, R_L = 50\Omega, C_L = 35pF$	-40°C to 105°C	-	-	20.0	ns
		Sopr See Test Circuit Figure 3.					
		$R_L = 50\Omega.$					
$f_{3dB}$	3dB Bandwidth	<i>RL</i> – 5052. See Test Circuit Figure 6.	+25°C	-	380		MHz
	COM-NC/NO and	$R_L = 50\Omega, f = 10MHz$					
OISO	NC-NO Isolations	See Test Circuit Figure 4.	+25°C	-	-68		dB
	Channel-to-Channel	$R_L = 50\Omega, f = 10MHz$					
XTALKD	Crosstalk	See Test Circuit Figure 5.	+25°C	-	-62		dB
X <sub>TALK(ADJ</sub>		$R_L = 50\Omega, f = 10MHz$					
TALK(ADJ	Crosstalk adjacent	See Test Circuit Figure 5.	+25°C	-	-91		dB
)	Power Supply Cur-	$V_{DD} = 3.6V, V_{IN} = 0V \text{ or}$					
I <sub>CC</sub>	rent	$V_{DD} = 3.0 \text{ V},  V_{IN} = 0 \text{ V}        $	-40°C to 105°C	-		3.0	μΑ
	TOIL			1	1		1

+25°C.)	+2.5V Supply ( $V_{DD} = 2.3V$ to 2.7	, $T_A = -40^{\circ}$ C to 105°C, unless otherwise noted.	Typical	values ar	e at 2.5V	and
	+25°C.)					

Symbol	Parameter	Test Conditions	ТЕМР	Min.	Тур.	Max.	Units		
ANALOG	ANALOG SWITCH								
V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>	Analog Signal Range		-40°C to 105°C	0	-	$V_{\text{DD}}$	V		
		$V_{DD}$ = 2.3V, $I_{COM}$ = -	+25°C	-	5.5	9.6			
R <sub>ON</sub>	On-Resistance	32mA, $0 \le V_{NO}$ or $V_{NC} \le V_{DD}$ , <i>Test Circuit 1</i>	-40°C to 105°C	-	-	11.5	Ω		
	On-Resistance	$V_{DD}$ = 2.3V, $I_{COM}$ = -	+25°C	-	0.3	0.8			
$\Delta R_{ON}$	Match Between Channels	32mA, $V_{NO}$ or $V_{NC} = 1.6V$ , Test Circuit 1	-40°C to 105°C	-	-	0.9	Ω		



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Symbol	Parameter	Test Conditions	TEMP	Min.	Тур.	Max.	Units
	0 D .	$V_{DD} = 2.3V, I_{COM} = -$	+25°C	-	0.91	2.2	
Ronf	On-Resistance Flatness	32mA, $V_{NO} = 0.15V$ or $V_{NC} = 2.15V$ , Test Circuit 1	-40°C to 105°C	-	-	2.3	Ω
I <sub>OFF (NO)</sub> or I <sub>OFF (NC)</sub>	NO/NC Channel- Off Leakage Current	$V_{DD} = 2.7V, V_{NO} \text{ or } V_{NC} = 2.3V \& V_{COM} = 0.5V \text{ or} V_{NO} \text{ or } V_{NC} = 0.5V \& V_{COM} = 2.3V$	-40°C to 105°C	-6	-	6	μΑ
IOFF (COM)	COM Channel-Off Leakage Current	$V_{DD} = 2.7V, V_{NO} \text{ or } V_{NC} = 2.3V \& V_{COM} = 0.5V \text{ or} V_{NO} \text{ or } V_{NC} = 0.5V \& V_{COM} = 2.3V$	-40°C to 105°C	-1	-	1	μΑ
I <sub>OFF (NO)</sub> or I <sub>OFF (NC)</sub>	NC/NO POWER- Off Leakage Current		-40°C to 105°C	-10	-	10	μΑ
I <sub>OFF (COM)</sub>	COM POWER-Off Leakage Current		-40°C to 105°C	-7.2	-	7.2	μΑ
I <sub>ON</sub> (NO) or I <sub>ON</sub> (NC)	Channel-On Leak- age Current (NO/NC)	$V_{DD} = 2.7V, V_{NO} \text{ or } V_{NC} = 2.3V \& V_{COM} = \text{ open or} V_{NO} \text{ or } V_{NC} = 0.5V \& V_{COM} = \text{ open}$	-40°C to 105°C	-6	-	6	μΑ
I <sub>ON</sub> (COM)	Channel-On Leak- age Current (COM)	$V_{DD} = 2.7V, V_{NO} \text{ or } V_{NC} =$ open &V_{COM} = 2.3V or $V_{NO} \text{ or } V_{NC} =$ open & $V_{COM} = 0.5V$	-40°C to 105°C	-5.7	-	5.7	μΑ
DIGITAL					1		
V <sub>IH</sub> V <sub>IL</sub>	Input Logic High Input Logic Low	-	-40°C to 105°C -40°C to 105°C	0.8	-	3.6 0.2	V
I <sub>IN</sub>	IN Input Leakage Current	$V_{DD} = 2.7V, V_{IN} = 0$ or 2.7V	-40°C to 105°C	-2.5	-	2.5	μA
DYNAMI	C CHARACTERISTI						
		$V_{DD} = 2.3V$ to 2.7V, $V_{COM}$ = $V_{DD}$ , $R_L = 50\Omega$ , $C_L =$	+25°C	-	17.2	36.8	
t <sub>ON</sub>	Turn-On Time	35pF See Test Circuit Figure 2.	-40°C to 105°C	-	-	42.5	ns
	<b>T</b> 0.00 <b>T</b>	$V_{DD} = 2.3V$ to 2.7V, $V_{COM}$ = $V_{DD}$ , $R_L = 50\Omega$ , $C_L =$	+25°C	-	17.1	29.8	
toff	Turn-Off Time	35pF See Test Circuit Figure 2.	-40°C to 105°C	-	-	38.4	ns
		$V_{DD} = 2.3V$ to 2.7V, $V_{COM}$	+25°C	4.5	13	30	
t <sub>D</sub>	Break-Before-Make Delay	= $V_{DD}$ , $R_L = 50\Omega$ , $C_L = 35pF$ See Test Circuit Figure 3.	-40°C to 105°C	-	-	33.3	ns
Qc	Charge Injection	$V_{GEN} = 0, R_{GEN} = 0, C_L = 0.1nF, See Test Circuit Figure 9$	+25°C	-	0.47	-	pC
$f_{3dB}$	3dB Bandwidth	$R_L = 50\Omega.$ See Test Circuit Figure 6.	+25°C	-	380	-	MHz
O <sub>ISO</sub>	COM-NC/NO and NC-NO Isolations	$R_L = 50\Omega$ , f = 10MHz See Test Circuit Figure 4.	+25°C	-	-66	-	dB
X <sub>TALKD</sub>	Channel-to-Channel Crosstalk	$R_L = 50\Omega$ , f = 10MHz See Test Circuit Figure 5.	+25°C	-	-60	-	dB





Symbol	Parameter	<b>Test Conditions</b>	TEMP	Min.	Тур.	Max.	Units
)		See Test Circuit Figure 5.					
I <sub>CC</sub>	Power Supply Cur- rent	$V_{DD} = 2.7V$ , $V_{IN} = 0V$ or $V_{DD}$ , Switch ON or OFF	-40°C to 105°C	-	-	3.0	μΑ

# +1.8V Supply ( $V_{DD}$ = 1.65V to 1.95V, $T_A$ = -40°C to 105°C, unless otherwise noted. Typical values are at 1.8V and +25°C.)

Symbol	Parameter	Test Conditions	TEMP	Min.	Тур.	Max.	Units
	SWITCH						
V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>	Analog Signal Range		-40°C to 105°C	0	-	$V_{\text{DD}}$	V
R <sub>ON</sub>	On-Resistance	$V_{DD} = 1.65 V$ , $I_{COM} = -$ 32mA, $0 \le V_{NO}$ or $V_{NC} \le$	+25°C	-	7.1	14.4	Ω
KON	On-Resistance	$V_{DD}$ , Test Circuit 1	-40°C to 105°C	-	-	16.3	52
1.5	On-Resistance	$V_{DD} = 1.65 V$ , $I_{COM} = -$	+25°C	-	0.3	1	
$\Delta R_{ON}$	Match Between Channels	32mA, $V_{NO}$ or $V_{NC} = 1.5V$ , Test Circuit 1	-40°C to 105°C	-	-	1.2	Ω
	On-Resistance	$V_{DD} = 1.65 V, I_{COM} = -$	+25°C	-	2.7	5.5	
R <sub>ONF</sub>	Flatness	$32$ mA, $V_{NO} = 0.15$ V or $V_{NC}$ = 1.5V, <i>Test Circuit 1</i>	-40°C to 105°C	-	-	7.3	Ω
$I_{OFF (NO)}$ or $I_{OFF (NC)}$	NO/NC Channel- Off Leakage Current	$V_{DD} = 1.95V, \\ V_{NO} \text{ or } V_{NC} = 1.65V \& \\ V_{COM} = 0.3V \text{ or } V_{NO} \text{ or } \\ V_{NC} = 0.3V \& V_{COM} = \\ 1.65V$	-40°C to 105°C	-0.9	-	0.9	μΑ
$I_{OFF (COM)}$	COM Channel-Off Leakage Current	$V_{DD} = 1.95V, \\ V_{NO} \text{ or } V_{NC} = 1.65V \& \\ V_{COM} = 0.3V \text{ or } V_{NO} \text{ or } \\ V_{NC} = 0.3V \& V_{COM} = 1.65V$	-40°C to 105°C	-0.9	-	0.9	μΑ
$I_{OFF (NO)}$ or $I_{OFF (NC)}$	NC/NO POWER- Off Leakage Current		-40°C to 105°C	-5	-	5	μΑ
IOFF (COM)	COM POWER-Off Leakage Current		-40°C to 105°C	-5	-	5	μΑ
I <sub>ON</sub> (NO) or I <sub>ON</sub> (NC)	Channel-On Leak- age Current (NO/NC)	$V_{DD} = 1.95V,$ $V_{NO} \text{ or } V_{NC} = 1.65V$ $\&V_{COM} = \text{ open or } V_{NO} \text{ or }$ $V_{NC} = 0.3V \& V_{COM} = $ open	-40°C to 105°C	-5.2	-	5.2	μΑ
I <sub>ON</sub> (COM)	Channel-On Leak- age Current (COM)	$V_{DD} = 1.95V,$ $V_{NO} \text{ or } V_{NC} = \text{ open } \&$ $V_{COM} = 1.65V \text{ or } V_{NO} \text{ or}$ $V_{NC} = \text{ open } \& V_{COM} =$ 0.3V	-40°C to 105°C	-5.2	-	5.2	μΑ
DIGITAL							
VIH	Input Logic High	-	-40°C to 105°C	0.8	-	1.95	v
V <sub>IL</sub> I <sub>IN</sub>	Input Logic Low IN Input Leakage	- V <sub>DD</sub> = 1.95V, V <sub>IN</sub> = 0 or	-40°C to 105°C -40°C to 105°C	0	-	0.2	μΑ
	Current	1.95V					· ·
T <sub>ON</sub>	Turn-On Time	$V_{DD} = 1.65 V$ to 1.95 V,	+25°C	-	18.9	45	ns



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Symbol	Parameter	Test Conditions	ТЕМР	Min.	Тур.	Max.	Units
		$V_{COM} = V_{DD}, R_L = 50\Omega, C_L$ = 35pF See Test Circuit Figure 2.	-40°C to 105°C	-	-	45	
		$V_{DD} = 1.65V$ to 1.95V,	+25°C	-	14.0	26	
T <sub>OFF</sub>	Turn-Off Time	$V_{COM} = V_{DD}, R_L = 50\Omega, C_L$ = 35pF See Test Circuit Figure 2.	-40°C to 105°C	-	-	26	ns
		$V_{DD} = 1.65V$ to 1.95V,	+25°C	5.3	11.8	40	
T <sub>D</sub>	Break-Before-Make Delay	$V_{COM} = V_{DD}, R_L = 50\Omega, C_L$ = 35pF See Test Circuit Figure 3.	-40°C to 105°C	-	-	40	ns
f <sub>3dB</sub>	3dB Bandwidth	$R_L = 50\Omega.$ See Test Circuit Figure 6.	+25°C	-	380	-	MHz
O <sub>ISO</sub>	COM-NC/NO and NC-NO Isolations	$R_L = 50\Omega$ , f = 10MHz See Test Circuit Figure 4.	+25°C	-	-66.0	-	dB
X <sub>TALKD</sub>	Channel-to-Channel Crosstalk	$R_L = 50\Omega$ , f = 10MHz See Test Circuit Figure 5.	+25°C	-	-60.0	-	dB
X <sub>TALK(ADJ</sub> )	Crosstalk adjacent	$R_L = 50\Omega$ , f = 10MHz See Test Circuit Figure 5.	+25°C	-	-91.0	-	dB
I <sub>CC</sub>	Power Supply Cur- rent	$V_{DD} = 1.95V$ , $V_{IN} = 0V$ or $V_{DD}$ , Switch ON or OFF	-40°C to 105°C	-	-	1.5	μΑ

# Capacitance

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
C <sub>NC (OFF)</sub> , C <sub>NO (OFF)</sub>	NC/NO Off Capac- itance	$V_{NC}$ or $V_{NO} = V_{DD}$ or GND, Switch OFF $f = 1MHz$ , See Test Circuit Figure 7.	-	10	-	
C <sub>COM</sub> (OFF)	COM Off Capaci- tance	$V_{COM} = V_{DD}$ or GND, Switch OFF f = 1MHz, See Test Circuit Figure 7.	-	16	-	ъE
C <sub>NC (ON)</sub> , C <sub>NO (ON)</sub>	NC/NO On Capaci- tance	$V_{NC}$ or $V_{NO} = V_{DD}$ or GND, Switch ON $f = 1MHz$ , See Test Circuit Figure 8.	-	21.5	-	pF
C <sub>COM</sub> (ON)	COM On Capaci- tance	$V_{COM} = V_{DD}$ or GND, Switch ON f = 1MHz, See Test Circuit Figure 8.	-	21.5	-	
C <sub>IN</sub>	Digital Input Ca- pacitance	f = 1MHz	-	3	-	pF





# **Test Circuits and Timing Diagrams**



#### Figure 1. ON Resistance

#### Notes:

1. Unused input (NC or NO) must be grounded.



Figure 2. Switching Times











Figure 4. OFF Isolation (OISO)



Figure 5. Channel-to-Channel Crosstalk



Figure 6. Bandwidth







Figure 7. Channel Off Capacitance



Figure 8. Channel On Capacitance



Figure 9. Charge Injection (Qc)





## **Part Marking**

Top mark not available at this time. To obtain advance information regarding the top mark, please contact your local sales representative.





## **Packaging Mechanical**



#### For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

#### **Ordering Information**

Part Number	Package Code	Package Description
PI3A27518Q2ZDWEX	ZDW	24-Contact, V-QFN4040-24 (SWP)

#### Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

- 4. Q = Automotive Compliant
- 5. 2 = AEC-Q100 Grade Level
- E = Pb-free and Green
- 7. X suffix = Tape/Reel





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